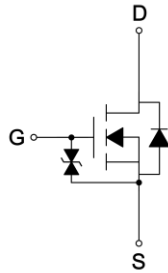
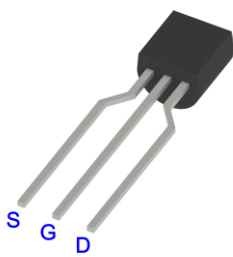


Product Summary

BV_{DSS}	60	V
$R_{DS(ON)}$ typ. @ $V_{GS}=10V, I_D=0.2A$	1.1	Ω
$R_{DS(ON)}$ typ. @ $V_{GS}=4.5V, I_D=0.2A$	1.2	
I_D @ $V_{GS}=10V, T_C=25^\circ C$	0.71	A
I_D @ $V_{GS}=10V, T_A=25^\circ C$	0.44	

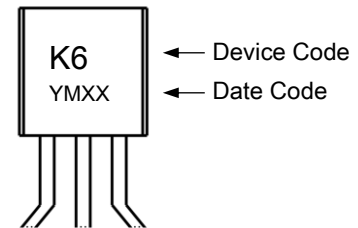
TO-92



Features

- Low Gate Charge
- Fast Switching Characteristic
- Pb-free lead plating and halogen-free
- ESD protected gate, typical 3kV (HBM)

Marking



YMXX: Date Code Marking

Y: Year Code, the last digit of Christian year

M: Month Code

A: Jan	B: Feb	C: Mar	D: Apr	E: May	F: Jun
G: Jul	H: Aug	J: Sep	K: Oct	L: Nov	M: Dec

XX: Production Serial Number, 01~99

Ordering Information

Device	Package	Shipping
MTNK6A3-0-TB-G	TO-92	2000pcs / Tape & Box

0: Product rank, zero for no rank products.

TB: Packing spec, TB : 2000pcs / Tape & Box

G: Environment friendly grade: S for RoHS compliant products, G for RoHS compliant and green compound products.

Absolute Maximum Ratings ($T_A=25^\circ C$)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V_{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current @ $V_{GS}=10V, T_C=25^\circ C$	I_D	0.71	A	
Continuous Drain Current @ $V_{GS}=10V, T_C=100^\circ C$		0.45		
Continuous Drain Current @ $V_{GS}=10V, T_A=25^\circ C$		0.44		
Continuous Drain Current @ $V_{GS}=10V, T_A=70^\circ C$		0.35		
Pulsed Drain Current	I_{DM}	1.5		
Continuous Body Diode Forward Current @ $T_C=25^\circ C$	I_S	0.7		
Pulsed Body Diode Forward Current @ $T_C=25^\circ C$	I_{SM}	1.5		
Total Power Dissipation	P_D	$T_C=25^\circ C$	2	W
		$T_C=100^\circ C$	0.8	
		$T_A=25^\circ C$	0.8	
		$T_A=70^\circ C$	0.5	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ C$	
Steady State Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	61	$^\circ C/W$	
Steady State Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	156		

Electrical Characteristics (T_A=25°C, unless otherwise specified)

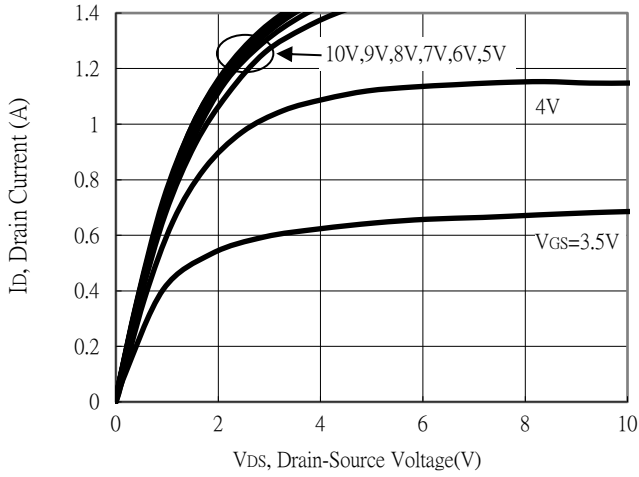
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	60	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1	-	2.5		V _{DS} =V _{GS} , I _D =250μA
G _{FS}	-	0.3	-	S	V _{DS} =10V, I _D =0.2A
I _{GSS}	-	-	±10	μA	V _{GS} =±16V, V _{DS} =0V
I _{DSS}	-	-	1		V _{DS} =48V, V _{GS} =0V
R _{DS(ON)}	-	1.1	2	Ω	V _{GS} =10V, I _D =0.2A
	-	1.2	3		V _{GS} =4.5V, I _D =0.2A
Dynamic					
C _{ISS}	-	25	-	pF	V _{DS} =30V, V _{GS} =0V, f=1MHz
C _{OSS}	-	9	-		
C _{ISS}	-	7	-		
R _g	-	3.3	-	Ω	f=1MHz
Q _g *d,e	-	0.75	-	nC	V _{DS} =30V, I _D =0.2A, V _{GS} =4.5V
Q _g *d,e	-	1.5	-		
Q _{gs} *d,e	-	0.45	-		
Q _{gd} *d,e	-	0.15	-		
t _{d(ON)} *d,e	-	4	-	ns	V _{DS} =30V, I _D =0.2A, V _{GS} =10V, R _{GS} =1Ω
t _r *d,e	-	15	-		
t _{d(OFF)} *d,e	-	10	-		
t _f *d,e	-	16	-		
Source-Drain Diode					
V _{SD} *d	-	0.8	1.2	V	I _S =0.2A, V _{GS} =0V
t _{rr}	-	9	-	ns	I _F =0.2A, di/dt=100A/μs
Q _{rr}	-	3	-	nC	

Note:

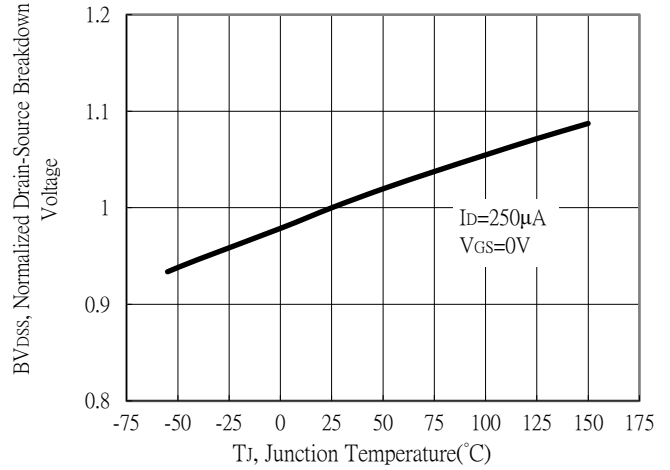
- *a. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper Dissipation.
- *b. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz copper, in a still air environment with T_A=25°C. The power dissipation P_D is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- *c. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.
- *d. Pulse Test : Pulse Width≤300μs, Duty Cycle≤2%.
- *e. Independent of operating temperature.

Typical Characteristics

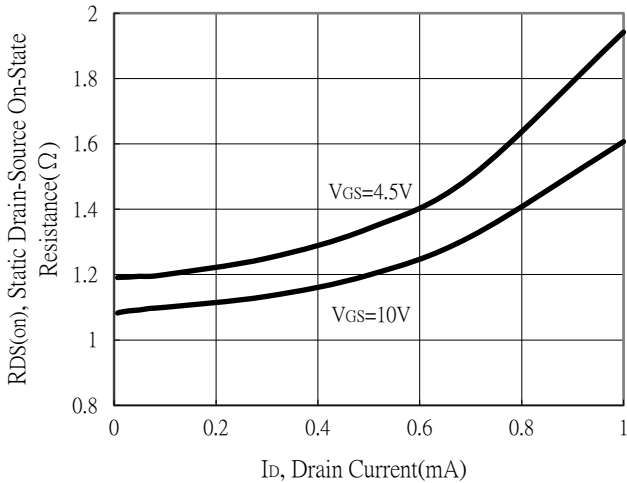
Typical Output Characteristics



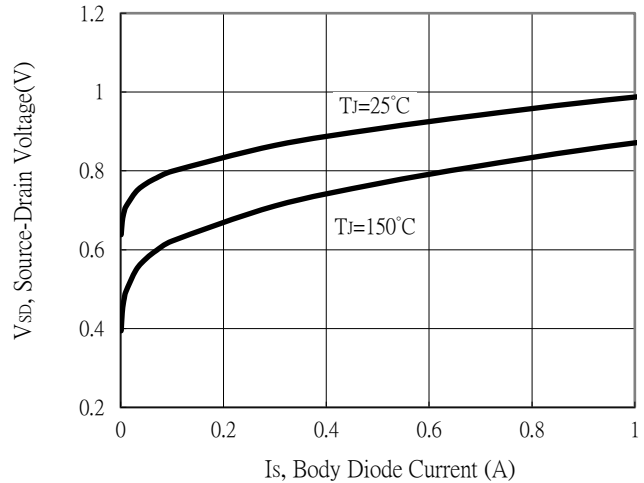
Breakdown Voltage vs Ambient Temperature



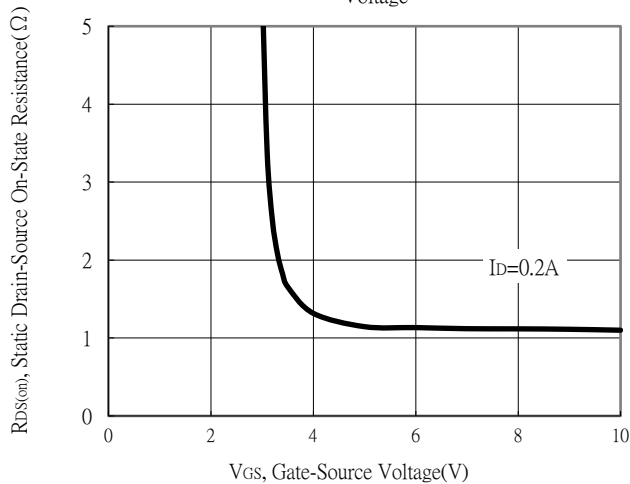
Static Drain-Source On-State resistance vs Drain Current



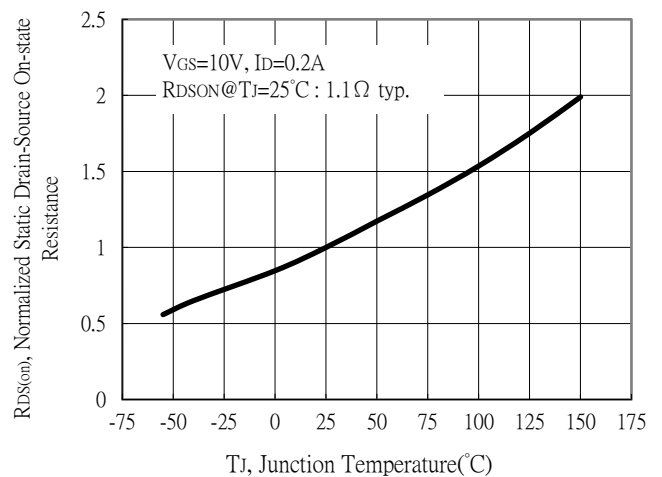
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

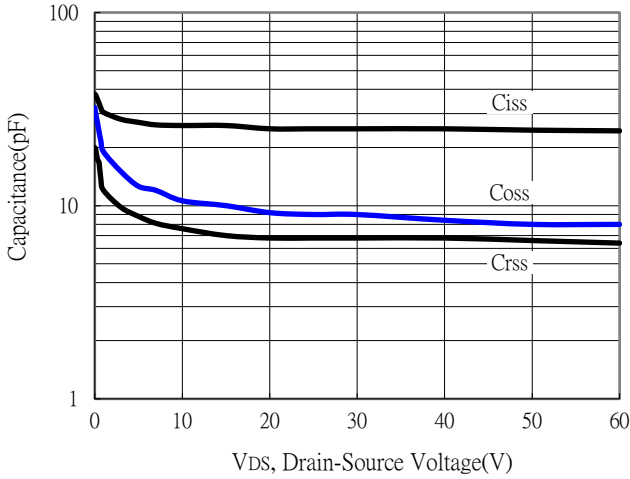


Drain-Source On-State Resistance vs Junction Temperature

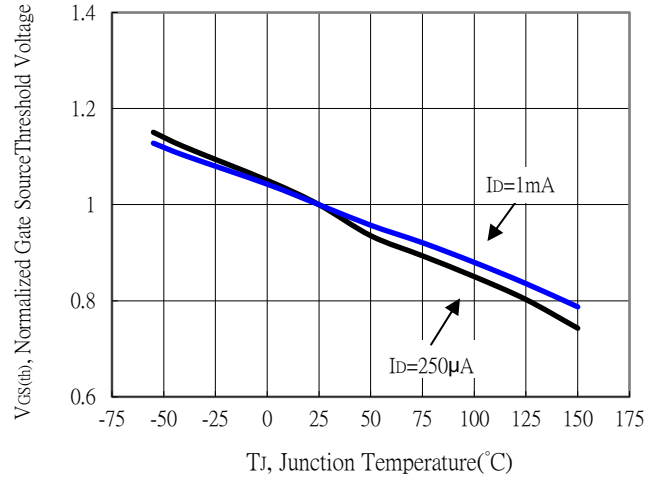


Typical Characteristics

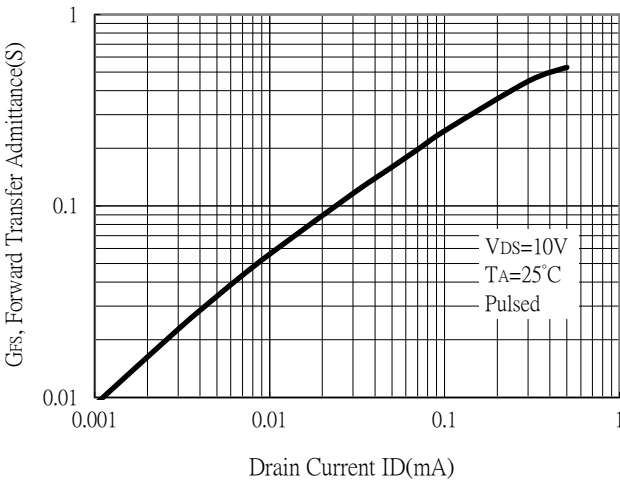
Capacitance vs Drain-to-Source Voltage



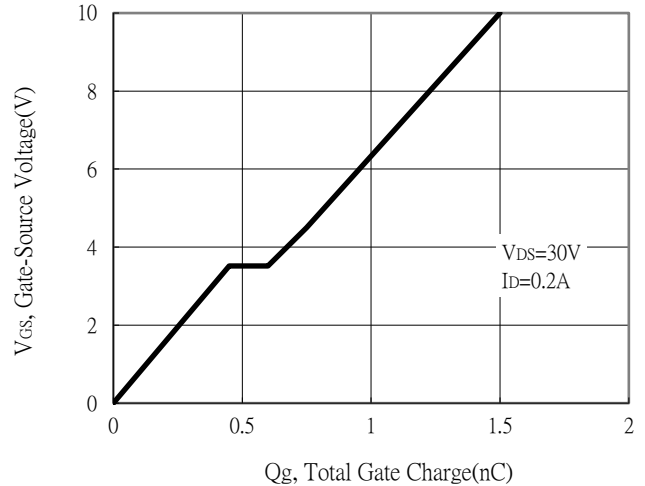
Threshold Voltage vs Junction Temperature



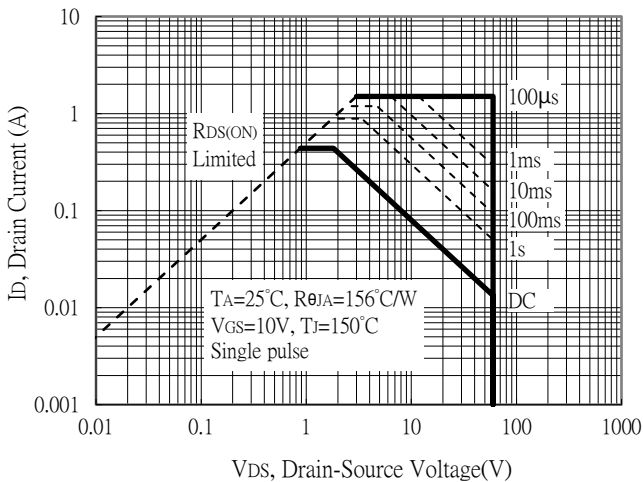
Forward Transfer Admittance vs Drain Current



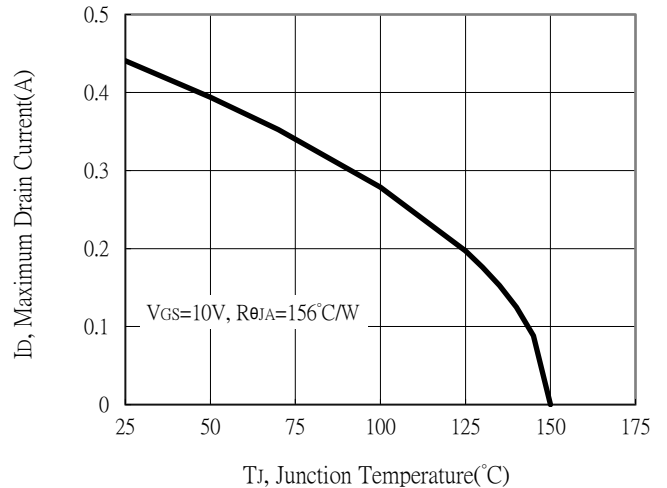
Gate Charge Characteristics



Maximum Safe Operating Area

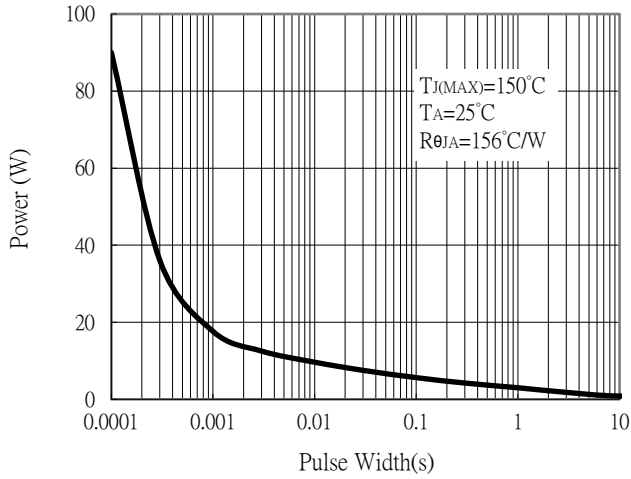


Maximum Drain Current vs Junction Temperature

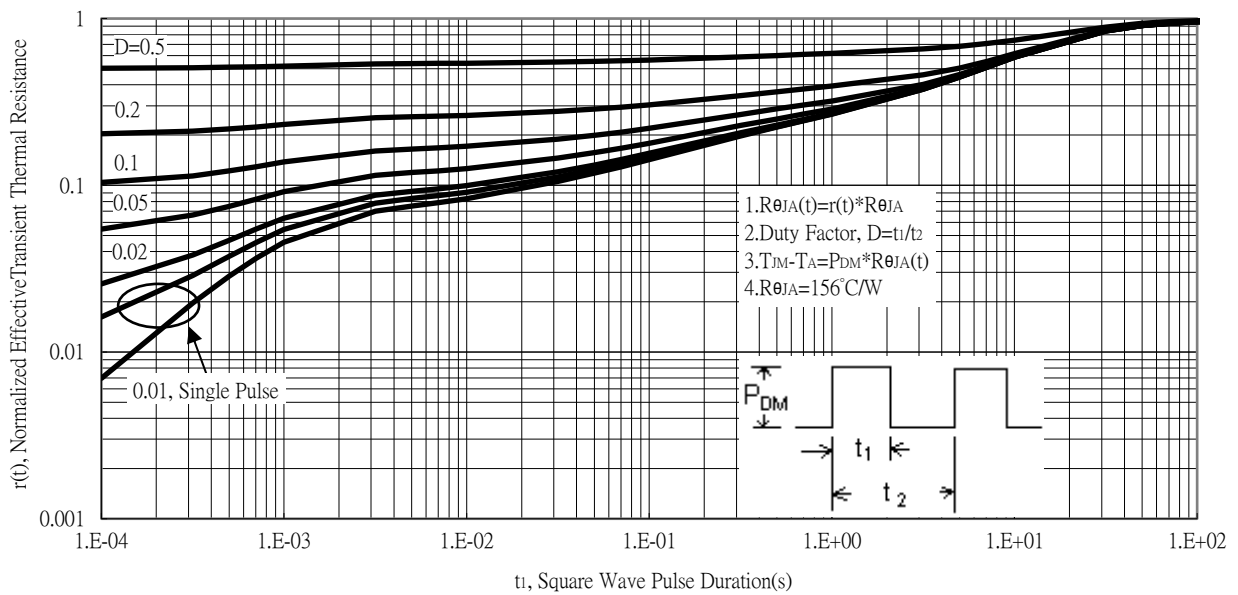


Typical Characteristics

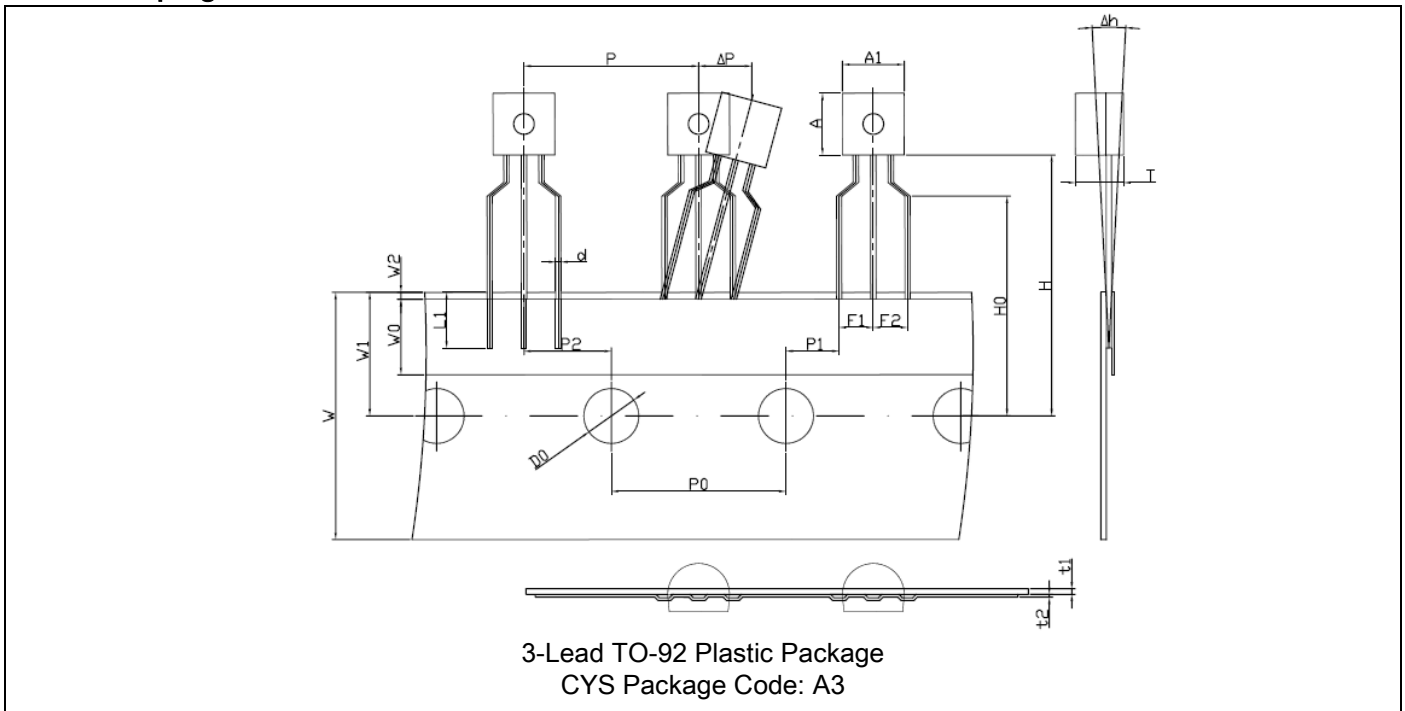
Single Pulse Power Rating, Junction to Ambient



Transient Thermal Response Curves



TO-92 Taping Outline Dimension

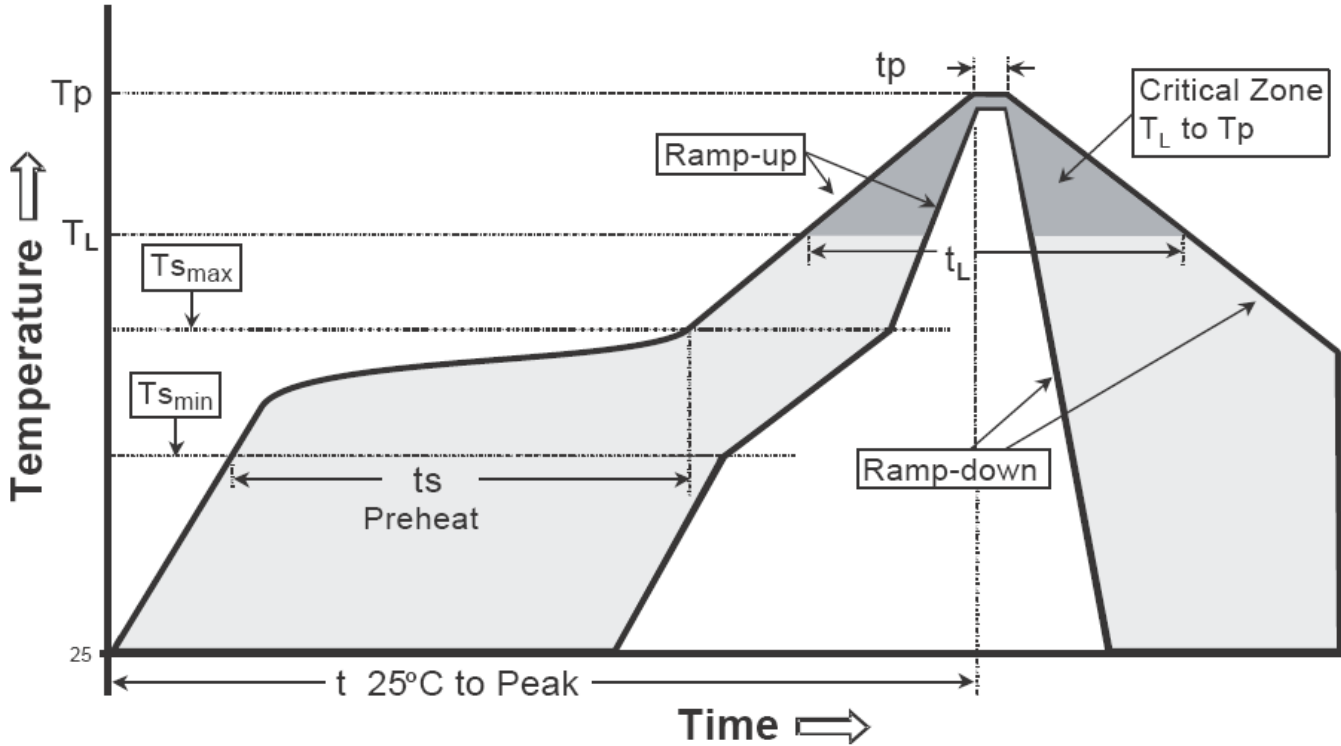


DIM	Item	Millimeters	
		Min.	Max.
A1	Body width	4.3	4.7
A	Body height	4.3	4.7
T	Body thickness	3.3	3.7
d	Lead wire diameter	0.38	0.55
P	Pitch of component	12.4	13
P0	Feed hole pitch	12.5	12.9
P2	Hole center to component center	6.05	6.65
F1,F2	Lead to lead distance	2.2	2.8
Δh	Component alignment, F-R	-1	1
W	Type width	17.5	19
W0	Hole down tape width	5.5	6.5
W1	Hole position	8.5	9.5
W2	Hole down tape position	-	1
H	Height of component from tape center	18	21
H0	Lead wire clinch height	15.5	16.5
L1	Lead wire(tape portion)	2.5	-
D0	Feed hole diameter	3.8	4.2
t1	Taped Lead Thickness	0.35	0.45
t2	Carrier Tape Thickness	0.15	0.25
P1	Position of hole	3.55	4.15
ΔP	Component alignment	-0.1	0.1

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _S max to T _P)	3°C/second max.	3°C/second max.
Preheat -Temperature Min (T _S min) -Temperature Max (T _S max) -Time (t _S min to t _S max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: -Temperature (T _L) -Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature (T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature (t _P)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note:

- All temperatures refer to topside of the package, measured on the package body surface.